## NSN 5961-01-047-9228



Transistor - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-047-9228 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 140.0 breakdown voltage, collector-to-base, emitter open and 120.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open and 140.0 breakdown voltage, collector to emitter, with specified voltage between base and emitter **Current Rating Per Characteristic:** Between 4.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 120.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure:** 

No

**Demilitarization:** 

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